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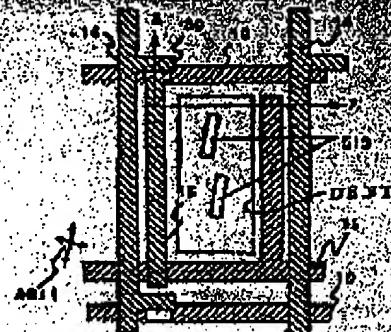
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(54) LIQUID CRYSTAL DISPLAY SUBSTRATE

(57) Abstract

PURPOSE: To improve a response speed and contrast ratio by forming dents in the region within a plane contg. a pair of electrodes.

CONSTITUTION: Gate electrodes 10 and common electrodes 16 are formed of Cr and formed on a glass substrate and gate insulating films consisting of silicon nitride films are so formed as to cover these electrodes. Amorphous silicon films 30 are formed via the gate insulating films on a part on the gate electrodes 10 and are used as active layers of transistors. The dents DENTS are formed in the regions within the plana inclusive of a pair of such electrodes. The more components of the transverse direction (direction connecting the respective electrodes of a pair of the electrodes are eventually capable of passing liquid crystals. The liquid crystals are packed into the regions formed with these dents DENTS and the packed liquid crystal layers are eventually brought into proximity with the plane contg. a pair of the electrodes or are made to exist down to the lower side (transparent substrate surface side formed with a pair of the electrodes) of the plane. Then, the response speed of the liquid crystals is improved and the sufficient contrast ratio is obt'd.



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